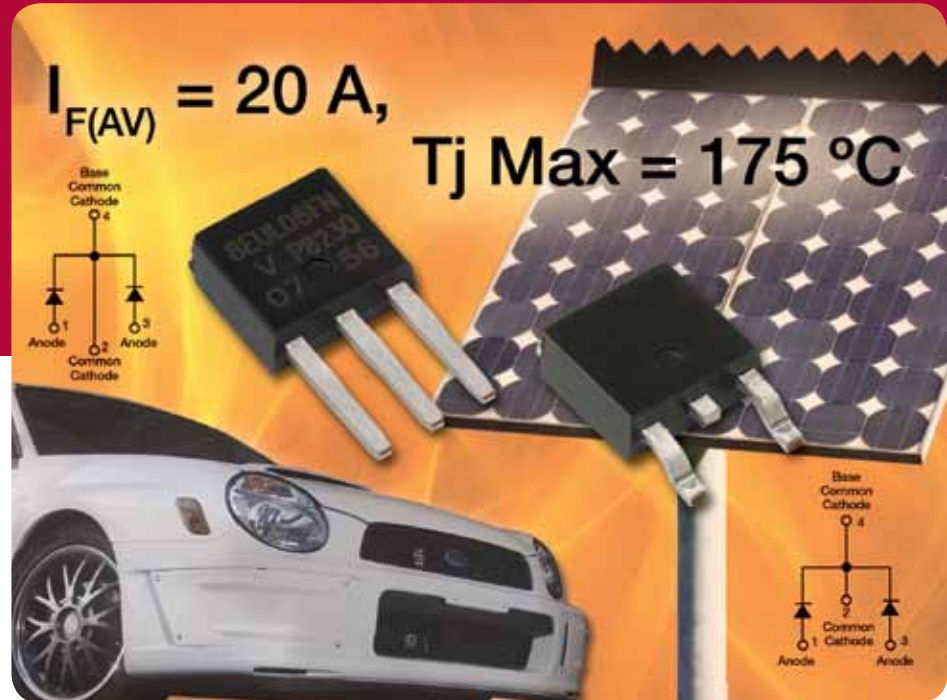




HIGH-PERFORMANCE GEN 5.0 SCHOTTKY DIODES

20WT04FN



Schottky Diodes Built on Submicron Trench Technology Feature Maximum Junction Temperature to + 175 °C and Low Reverse Leakage Down to 3 mA

KEY BENEFITS

- $T_{j,max} = 175\text{ °C}$
- Very low forward voltage drop (V_F max: 0.530 V at 20 A, 125 °C)
- Extremely low reverse leakage (I_R max: 7 mA at 45 V, 125 °C)
- Optimized V_F vs. I_R trade-off for high efficiency
- Increased ruggedness for reverse avalanche capability

APPLICATIONS

- PV cell bypass diodes
- High-efficiency SMPS
- Automotive AEC-Q101 qualified
- High-frequency switching
- Output rectification
- Reverse battery protection

